

METHOD OF FORMING BARRIER LAYER

Abstract

First, a substrate having at least a conducting layer is provided.

Then, a CVD process is performed to form the Ti/TiN barrier layer onto the conducting layer. An examination procedure is followed, and if particles are detected in the Ti/TiN barrier layer, then a re-work procedure is performed to remove the Ti/TiN barrier layer and to reform a new Ti/TiN barrier layer.